Abstract

Method for the simultaneous double-side grinding of a plurality of semiconductor wafers, and semiconductor wafer having outstanding flatness

The subject matter of the invention is a method for the simultaneous double-side grinding of a plurality of semiconductor wafers, wherein each semiconductor wafer lies such that it is freely moveable in a cutout of one of a plurality of carriers caused to rotate by means of a rolling apparatus and is thereby moved on a cycloidal trajectory, wherein the semiconductor wafers are machined in material-removing fashion between two rotating working disks, wherein each working disk comprises a working layer containing bonded abrasive. The method according to the invention makes it possible, by means of specific kinematics, to produce extremely planar semiconductor wafers, which are likewise the subject matter of the invention.